



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	Ι _D T _A = +25°C
-30V	$122m\Omega @ V_{GS} = -10V$	-2.7A
	190mΩ @ V _{GS} = -4.5V	-2.0A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

SOT23 D G G Top View Top View

Ordering Information (Note 5)

Part Number	Compliance	Case	Packaging
DMP3160L-7	Standard	SOT23	3000/Tape & Reel
DMP3160LQ-7	Automotive	SOT23	3000/Tape & Reel

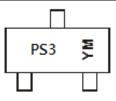
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

 Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/product-compliance-definitions/.
 For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} \mathsf{PS3} = \mathsf{Product} \ \mathsf{Type} \ \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} = \mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \mathsf{Y} \ \mathsf{or} \ \overline{\mathsf{Y}} = \mathsf{Year} \ (\mathsf{ex:} \ \mathsf{E} = 2017) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex:} \ 9 = \mathsf{September}) \end{array}$

Date Code Key

Notes:

Year	2007		20)17	2018	2019	2020	2021	1 20)22	2023	2024
Code	U			E	F	G	Н			J	K	L
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Character	istic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current (Note 6) $V_{GS} = -10V$ Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			۱ _D	-2.7 -2	А
Pulsed Drain Current (Note 7)			I _{DM}	-8	A

Thermal Characteristics

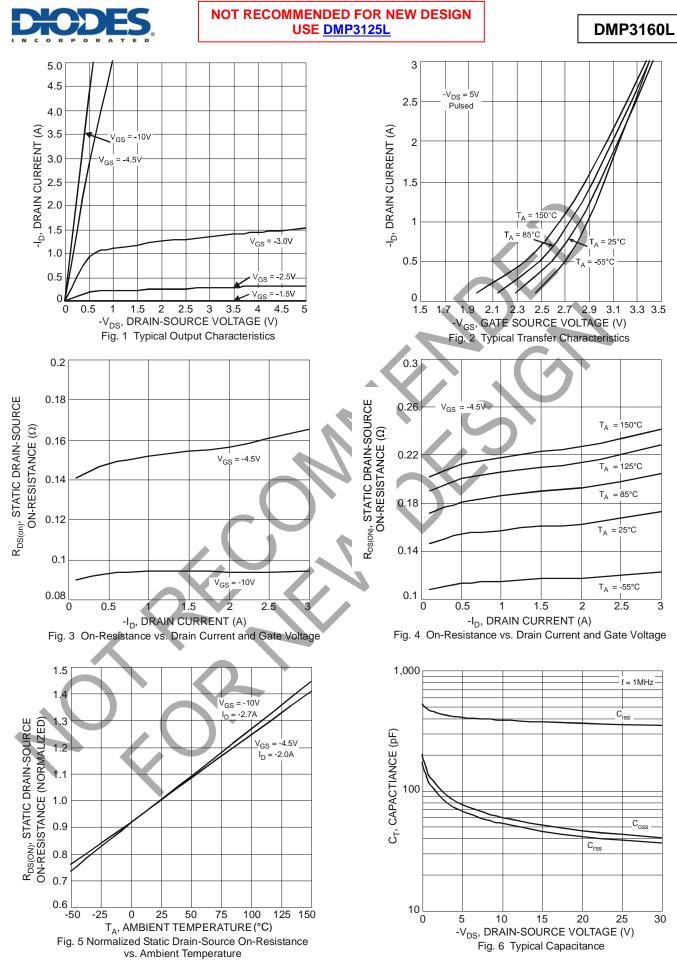
Characteristic	Symbol	Value	Unit				
Total Power Dissipation (Note 6)	PD	1.08	W				
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R _{0JA}	115	°C/W				
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C				

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—		V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	-800	nA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	IGSS	-		±80 ±800	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.3	-1.8	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}		97	122	mΩ	V_{GS} = -10V, I_{D} = -2.7A
	NDS(ON)		165	190	11152	V_{GS} = -4.5V, I_D = -2.0A
Forward Transfer Admittance	Y _{fs}		5.9	_	S	$V_{DS} = -5V, I_D = -2.7A$
Diode Forward Voltage (Note 8)	V _{SD}		—	-1.26	V	$V_{GS} = 0V, I_{S} = -2.7A$
DYNAMIC CHARACTERISTICS(Note 9)						
Input Capacitance	Ciss	_	384.4		pF	
Output Capacitance	C _{oss}	_	59.4		pF	V _{DS} = -10V, V _{GS} = 0V _ f = 1.0MHz
Reverse Transfer Capacitance	Crss		52.8		pF	
Gate Resistance	R _G	—	17.1	_	Ω	$\label{eq:VGS} \begin{array}{l} V_{GS} = 0V, \ V_{DS} = 0V, \\ f = 1.0MHz \end{array}$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	4.0	_	nC	
Total Gate Charge (V _{GS} = -10V)	Qg		8.2	_	nC	V _{GS} = -10V/-4.5V,
Gate-Source Charge	Q _{gs}	_	0.9	_	nC	$V_{DS} = -15V, I_{D} = -3A$
Gate-Drain Charge	Q _{gd}		1.2	_	nC	
Turn-On Delay Time	t _{D(ON)}		4.8		ns	
Turn-On Rise Time	t _R	_	7.3		ns	V _{DS} = -15V, V _{GS} = -10V,
Turn-Off Delay Time	t _{D(OFF)}	_	22.5		ns	$R_G = 6\Omega, I_D = -1A$
Turn-Off Fall Time	t _F	_	13.4		ns]

6. Device mounted on FR-4 PCB. t \leq 10 sec. Notes:

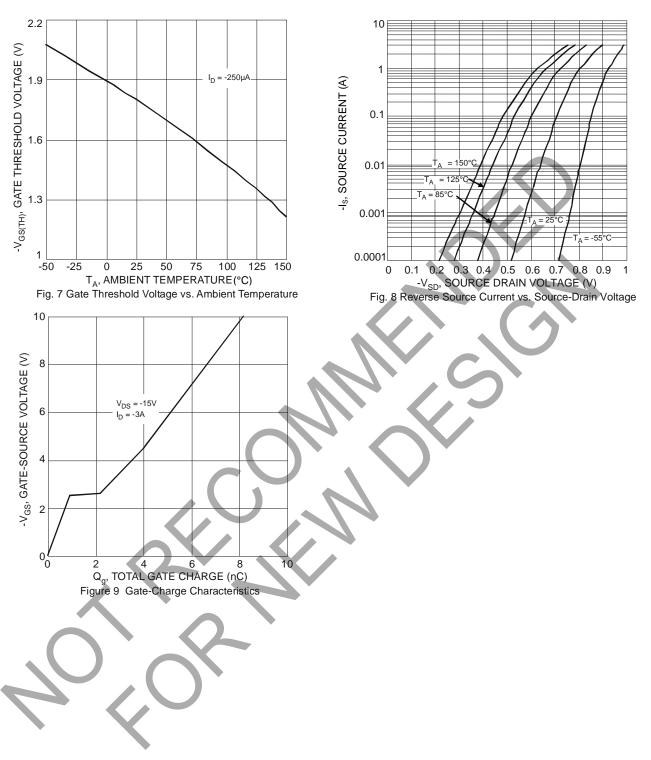
Pulse width ≤10µS, Duty Cycle ≤1%.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3125L</u>

DMP3160L

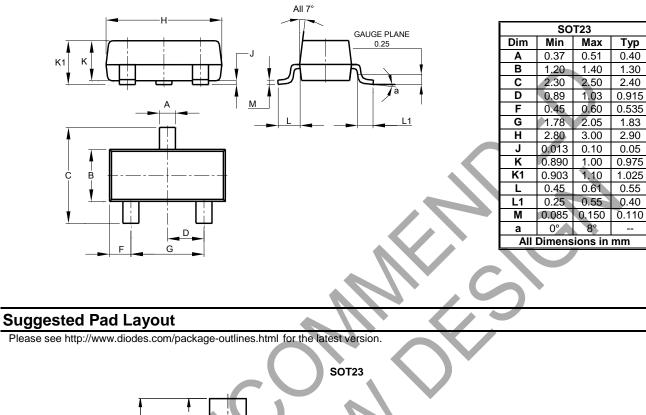




Package Outline Dimensions

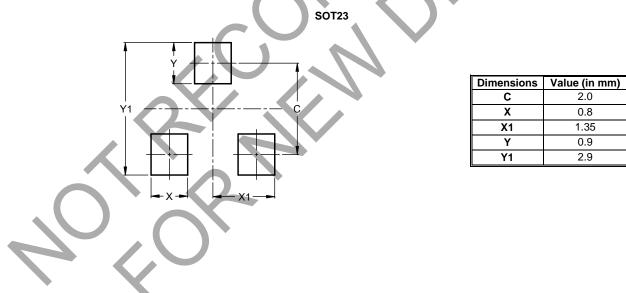
Please see http://www.diodes.com/package-outlines.html for the latest version.





Sugg	yeste	а саз	yout
		 12 1	

Please see http://www.diodes.com/package-outlines.html for the latest version.





IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below :

614233C 648584F D2003UK 705463DB MCH6422-TL-E FW231A-TL-E APT5010JFLL NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FQD4P40TM_AM002 FSS804-TL-E FW217A-TL-2W APT10050JVFR 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D1014UK D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM IRF3710 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IPS70R2K0CEAKMA1 APT8015JVFR APT50M85JVR APT5010JVFR APT12031JFLL APT12040JVR NTE6400 NVC385A51PLZT1G JANTX2N6796U JANTX2N6784U